



UFS 2.0 NAND Device Controller with SSD-Like Higher Read Performance

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Leading Innovation >>>

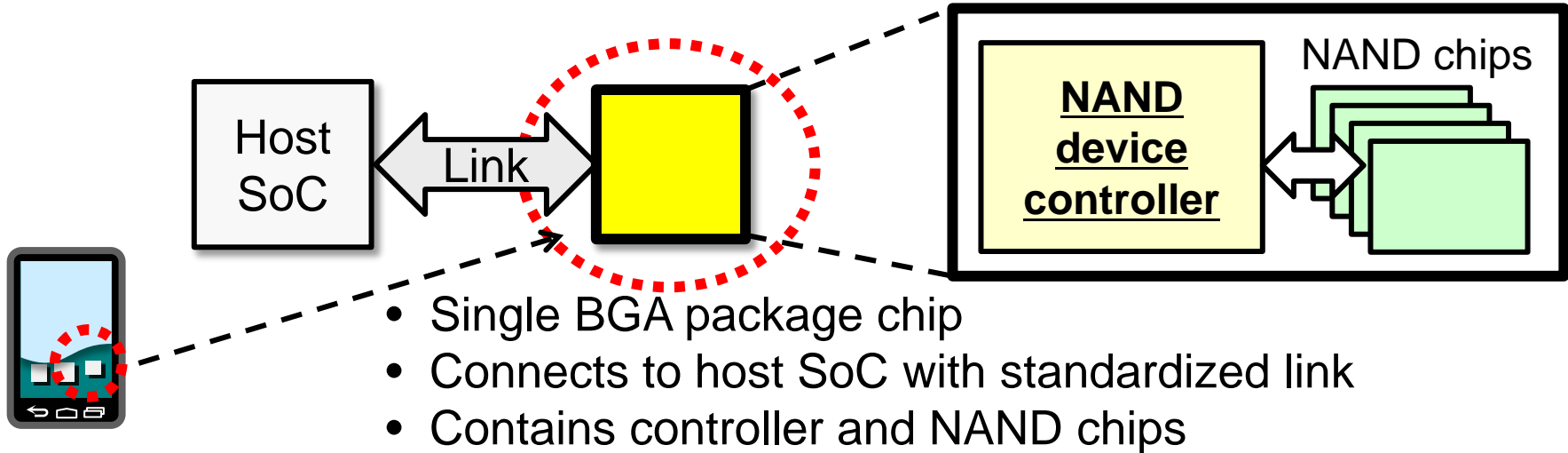
How did
our embedded NAND
storage device get
SSD-like
higher read performance?



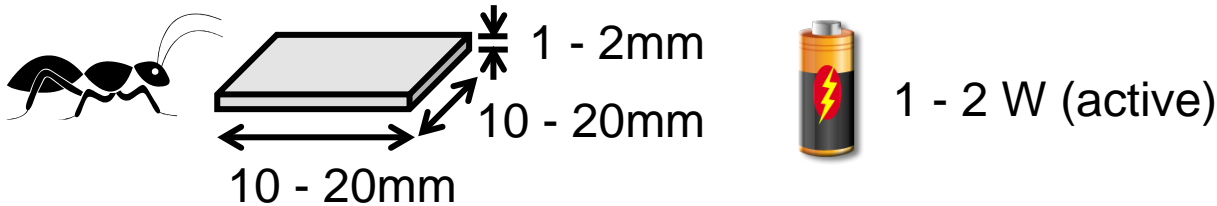
Flash Memory Summit Outline

- Background
- Approaches
- Example results

Embedded NAND Storage Device



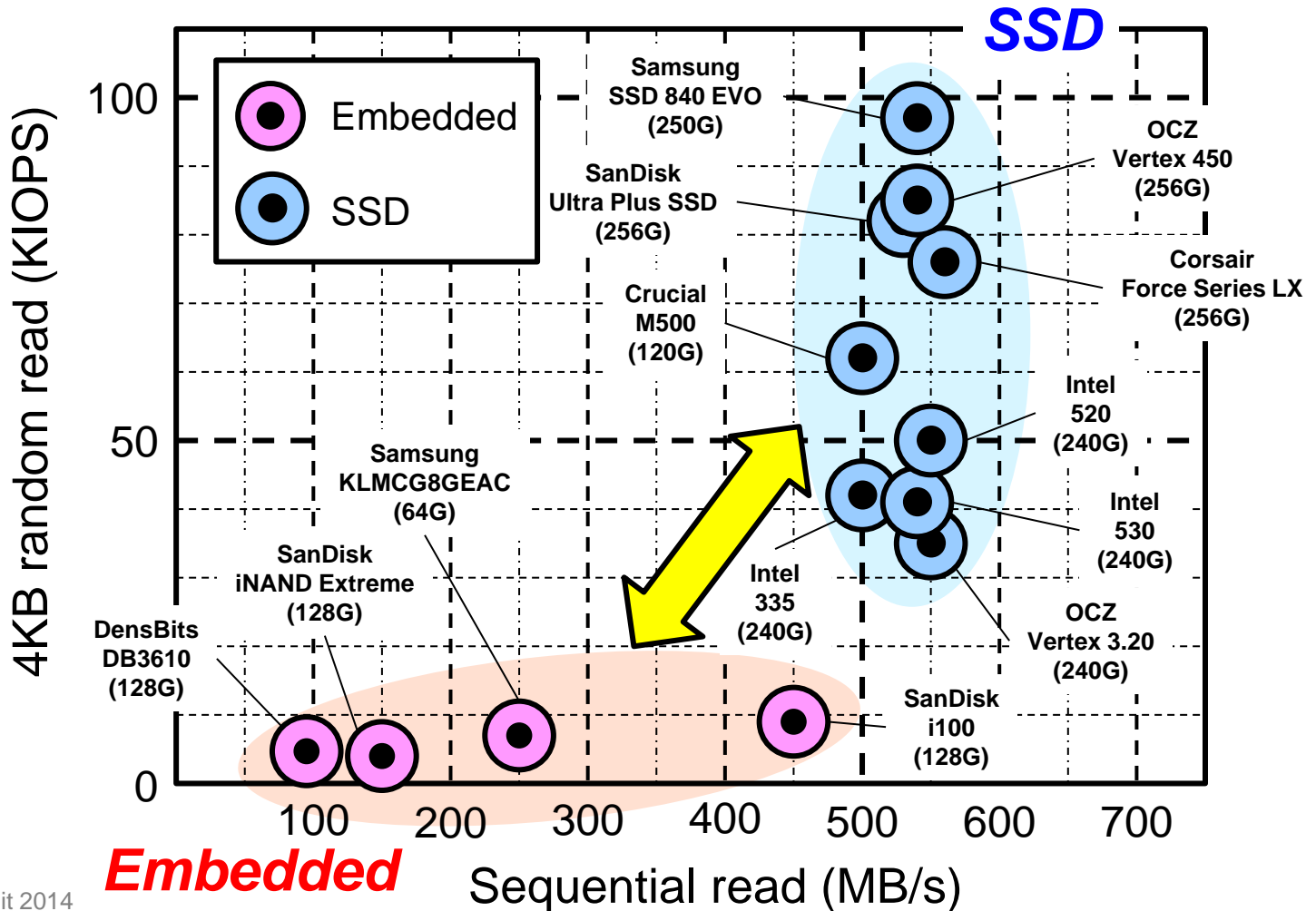
It must be **small** and **lower power**



...but now **higher performance** is also expected

UFS 2.0: 1160MB/s (5.8Gbps x 2-lane)

Performance of Current Embedded NAND Storage Device Products is Quite Low



Reason for Their Poor Performance and Our Challenge

- Embedded NAND storage device has strict limitation
 - It must be **small** and **lower power consumption**
 - Cannot take SSD's "rich man's" approach
 - Improve performance by utilizing rich resources
 - Massive NAND chips / channels
 - Powerful CPU
 - Large capacity RAM
- Goal: Achieve SSD-like higher performance without rich resources
 - Focused on read performance of UFS 2.0 device



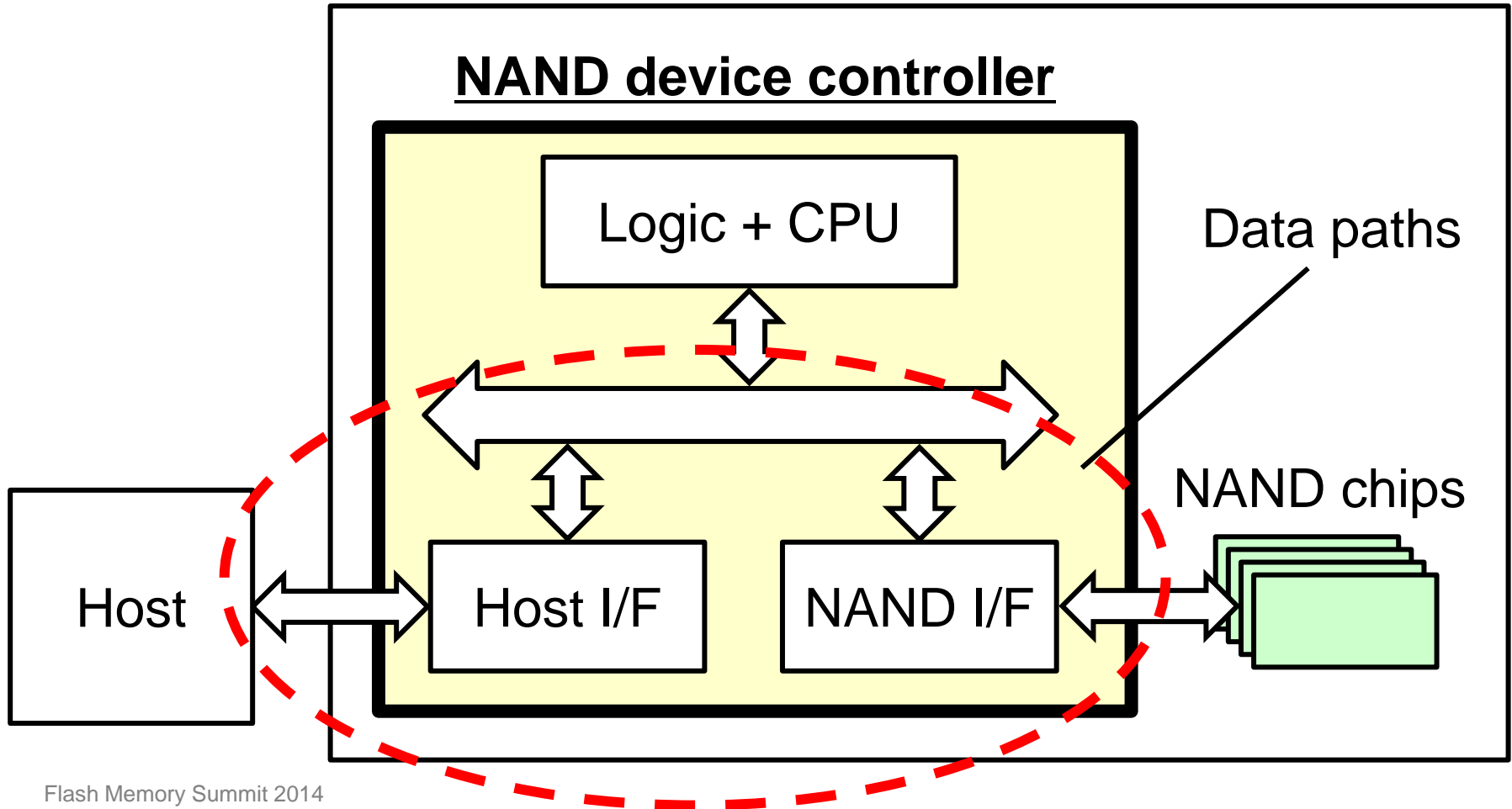
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Data Paths Strengthen (1)

Conventional NAND Device Controller

Embedded NAND storage device



Data Paths Strengthen (2) Strengthened Data Paths Minimally

Embedded NAND storage device

NAND device controller

Logic + CPU

800MB/s

400MB/s
x 2ch

NAND chips

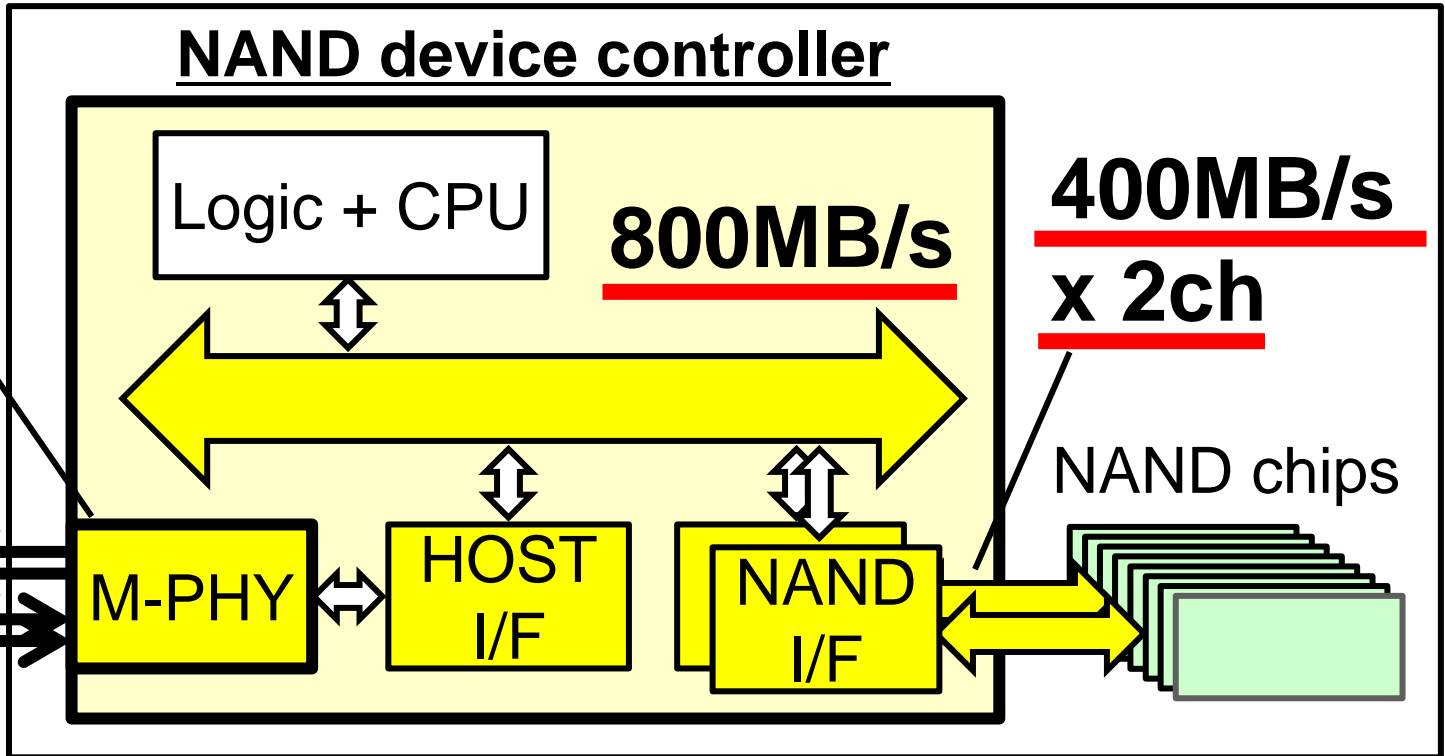
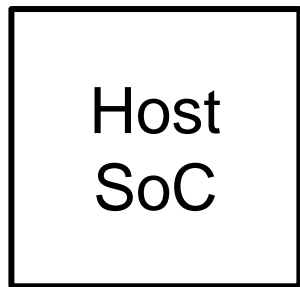
Host
SoC

M-PHY

HOST
I/F

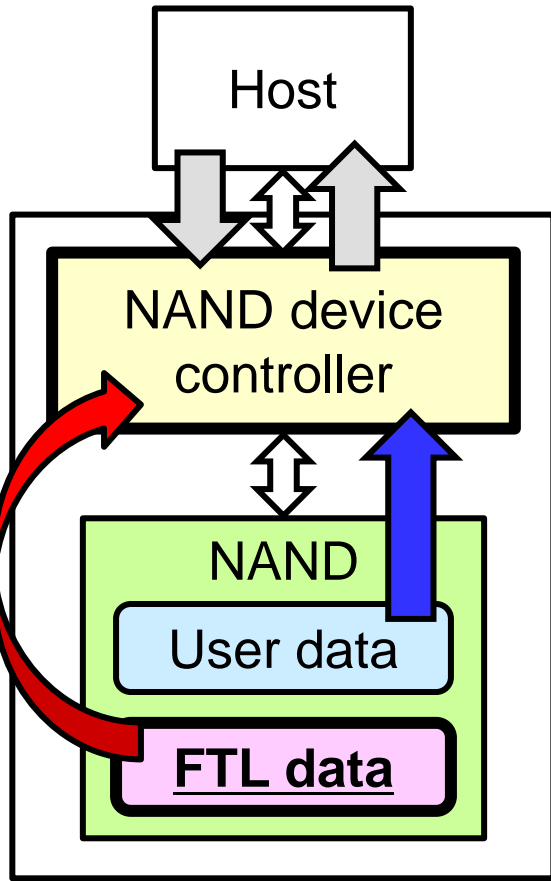
NAND
I/F

5.8Gbps
x 2-lane



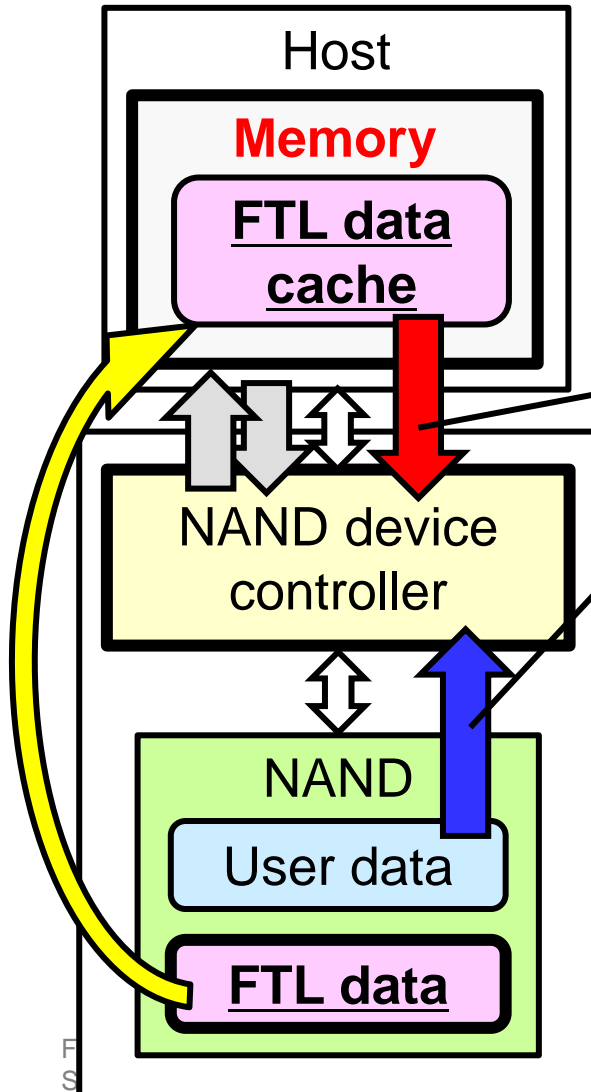
Random Read Latency Reduction (1)

Latency of Random Read



- Random read is accompanied by a couple of NAND reads
 - Target data (user data) read
 - A couple of FTL data reads
 - Special information for address translation
- NAND read latency is **several 10s μsec**
- Random read latency is larger than **100 μsec**
- Can be reduced by caching FTL data on large capacity RAM
 - With increasing of package size and power consumption

Random Read Latency Reduction (2) Using Unified Memory Architecture (UMA)



1. Made NAND device controller available to access host memory
 - Extended UFS standard
2. Cached FTL data on host memory

1. Reads host memory to get FTL data

2. Reads NAND to get user data

Host memory read latency

\ll NAND read latency



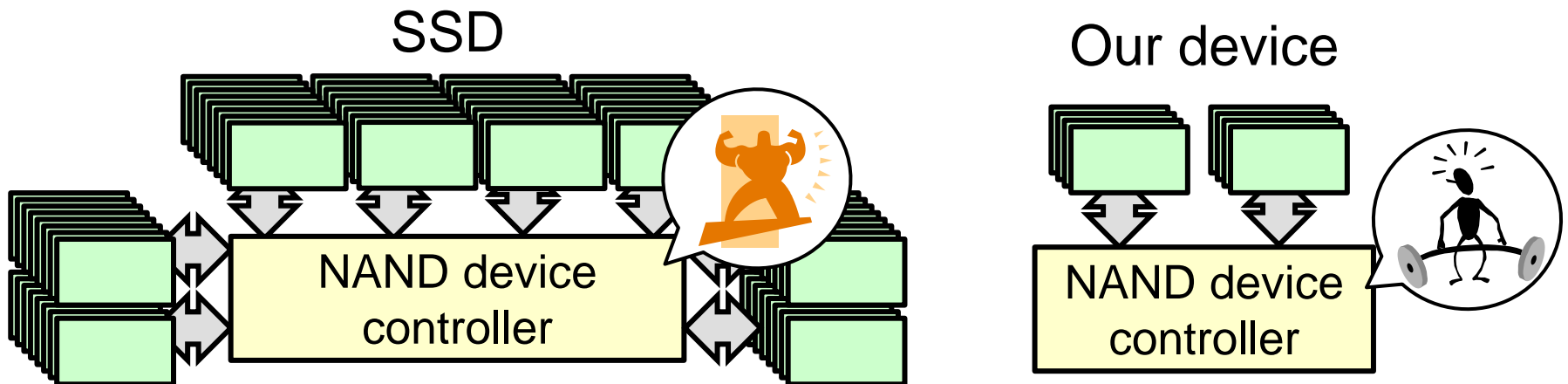
Reduces random read latency

by 50% in our evaluation environment

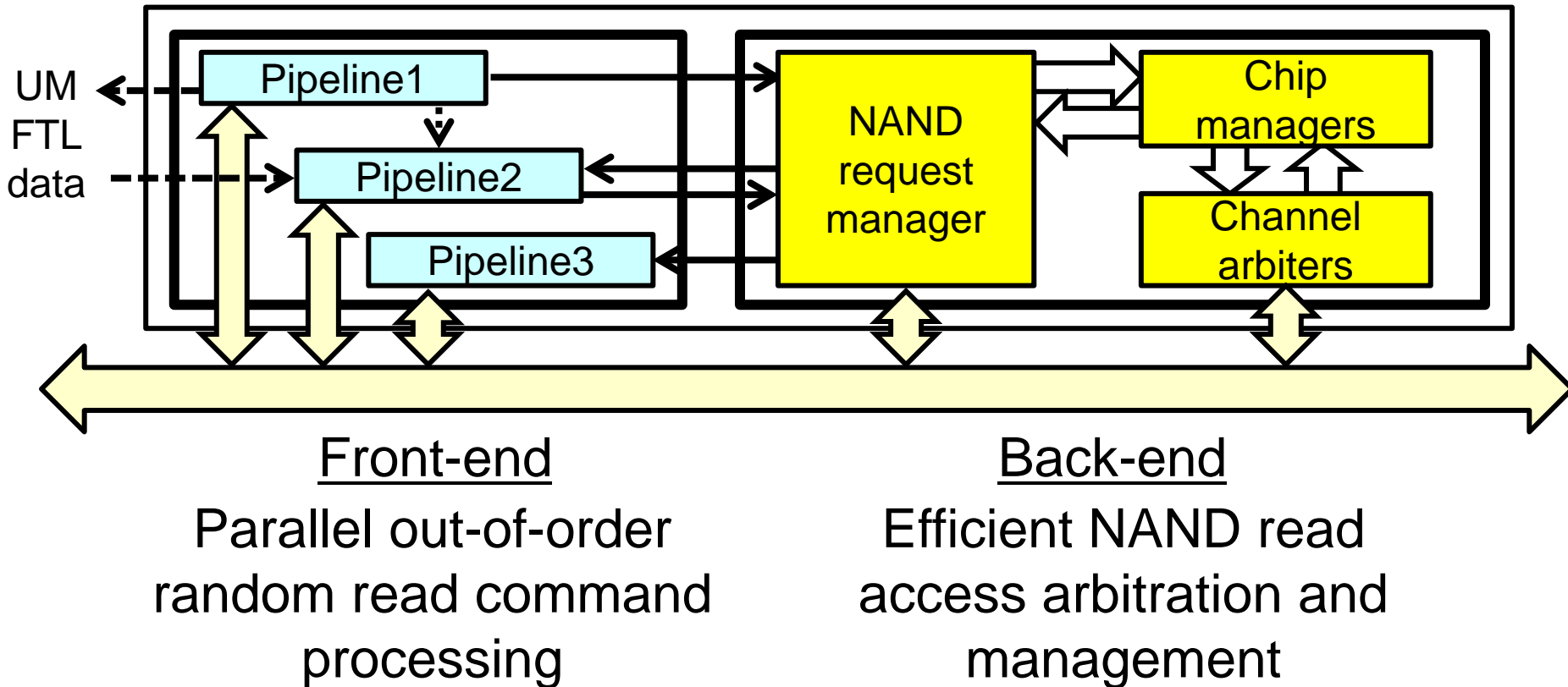
With no increase in package size and chip power consumption

Random Read Throughput Boost (1) Parallel NAND Reading

- NAND chips can be read in parallel
 - Multiple NAND chips (and channels)
 - Multiple outstanding NAND read requests
- Parallelism is determined by number of NAND chips, channels and read requests



Random Read Throughput Boost (2) Random Read Command Processor (RRCP)



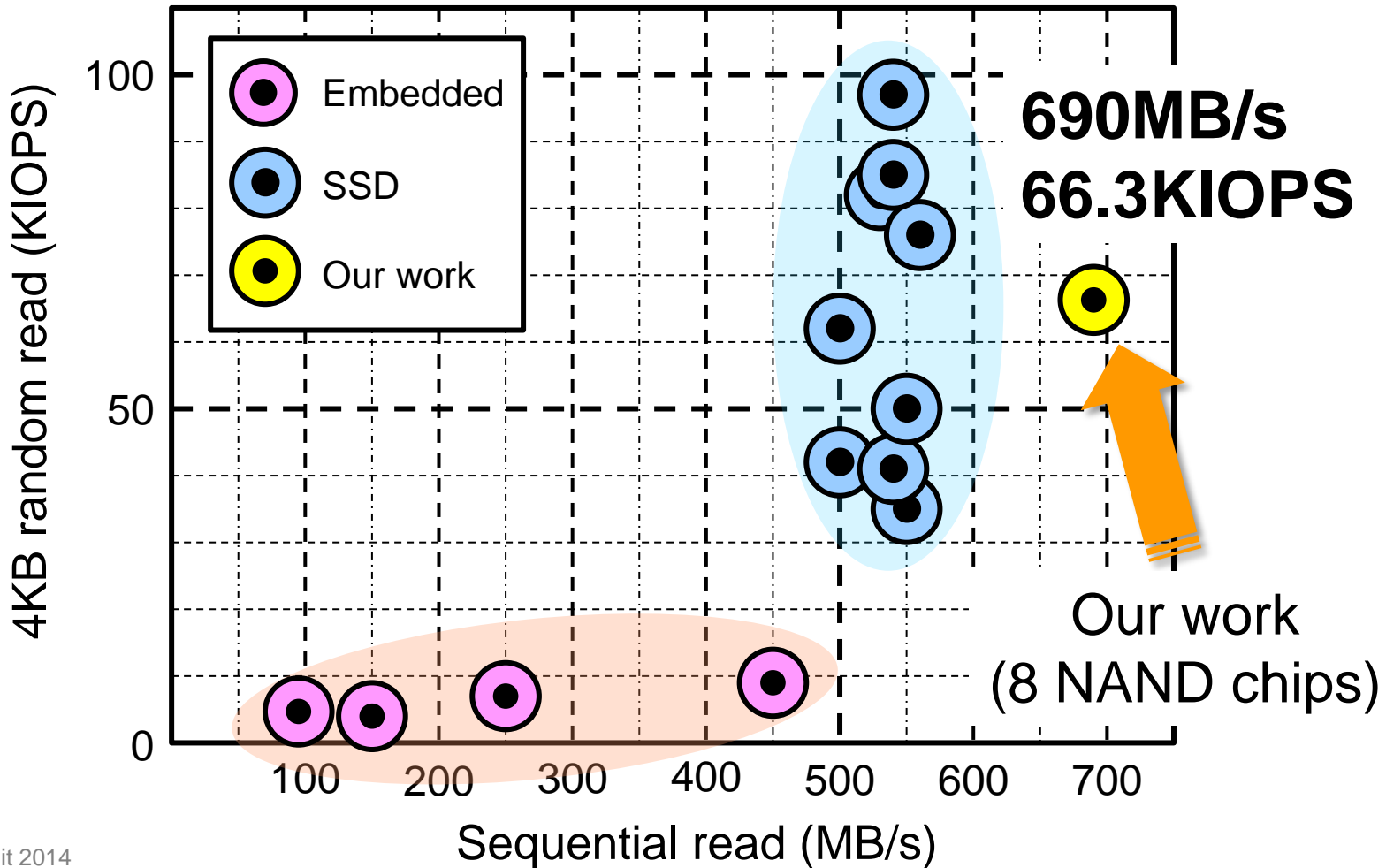
7.0 NAND chips are activated in parallel on average in our evaluation environment (with 8 NAND chips)



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SSD-like Read Performance is Achieved

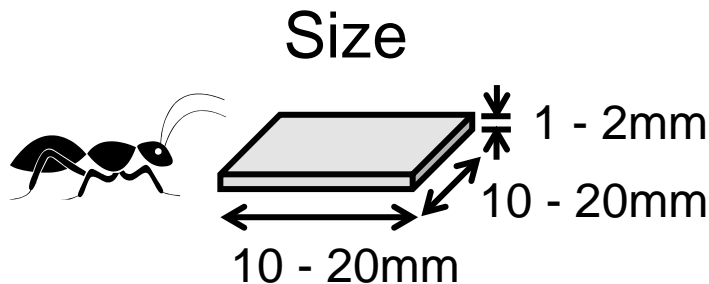


Package Size and Power Consumption can be Maintained

Package size (with NAND chips)		<u>11.5mm x 13.0mm x 1.2mm</u>
Package power	Active (Seq. read)	< <u>1.5 W</u> [‡]
	Idle / Sleep	< 1.45 mW [‡] / < 0.30 mW

‡ Depends on storage capacity

cf. Typical level



Power consumption



1 - 2 W (active)

Conclusion

- Developed UFS 2.0 embedded NAND storage device
- Improved read performance with three approaches
 - Strengthen data paths minimally
 - Reduce random read latency by using **unified memory architecture** and FTL data caching
 - Boost random read throughput by maximizing read command parallelism with **Random Read Command Processor**
- **SSD-like read performance** is achieved
 - 4KB random read: 66.3KIOPS
 - Sequential read: 690MB/s
- Package size and power consumption can be maintained
 - Package size (with NAND chips) : 11.5mm x 13.0mm x 1.2mm
 - Active (seq. read / write) : < 1.5 W